removing said oxide surface and said planarizing stop layer to expose a surface of said first orientation material of said first device region substantially planar with a surface of said second orientation material of said second device region.

14. The method of claim **10** wherein said forming said first concentration of lattice modifying material atop said first orientation material comprises epitaxially growing SiGe atop said first orientation material.

15. The method of claim **10** wherein said forming said second concentration of lattice modifying material atop said second orientation material comprises:

forming a protective layer atop said first concentration of lattice modifying material and atop said first orientation material;

forming a photoresist mask overlying said protective layer atop said first concentration of lattice modifying material atop said first orientation material, while leaving a remaining portion of said protective layer unprotected;

removing said remaining portion of said protective layer; and

epitaxially growing SiGe atop said second orientation material.

16. The method of claim **10** wherein said intermixing said first concentration of lattice modifying material with said first orientation to produce said first lattice dimension surface and said second concentration of lattice modifying material with said second orientation material to produce a second lattice dimension surface further comprises:

heating said first concentration of lattice modifying material, said first orientation material, said second concentration of lattice modifying material, and said second orientation material in an oxidizing environment to produce an oxidation layer atop said first lattice dimension surface and said second lattice dimensions surface;

forming a planarized layer atop said oxidation layer and said oxide material; and

etching said planarized layer and said oxidation layer to expose said first lattice dimension surface and said second lattice dimension surface.

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